

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Amended) A bipolar transistor, comprising:

a first semiconductor region of a first conductivity type defining a collector region;

a second semiconductor region of a second conductivity type defining a base region;

a third semiconductor region of said first conductivity type defining a emitter region; and

a metal layer providing contacts to said base and emitter regions;

wherein the transistor has a specific area resistance less than about $500\text{mQhm} \cdot \text{mm}^2$;

and

wherein said metal layer has a thickness greater than $3\mu\text{m}$.

2. (Original) A bipolar transistor according to claim 1, wherein the metal layer has a thickness no less than $4\mu\text{m}$.

3. (Amended) A bipolar transistor according to ~~any preceding claim~~, claim 1 wherein the metal layer has a thickness no less than $6\mu\text{m}$.

4. (Amended) A bipolar transistor according to ~~any preceding claim~~, claim 1 wherein the emitter region defines a first surface, the base region extending to said surface in locations defined by apertures through emitter region, said metal layer overlying said first surface.

5. (Original) A bipolar transistor according to claim 4, wherein adjacent apertures are spaced less than $100\mu\text{m}$ from each other.

6. (Canceled)